

Excalibur™ LOW-NOISE HIGH-SPEED PRECISION OPERATIONAL AMPLIFIER

FEATURES

- Qualified for Automotive Applications
- Low Noise
 - 10 Hz: 15 nV/ $\sqrt{\text{Hz}}$ - 1 kHz: 10.5 nV/ $\sqrt{\text{Hz}}$
- 10000-pF Load Capability
- 20-mA Short-Circuit Output Current (Min)
- 27-V/μs Slew Rate (Min)
- High Gain-Bandwidth Product: 5.9 MHz
- Single or Split Supply: 4 V to 44 V
- Fast Settling Time
 - 340 ns to 0.1%
 - 400 ns to 0.01%
- Large Output Swing:
 V_{CC} + 0.1 V to V_{CC+} 1 V

DESCRIPTION/ORDERING INFORMATION

The TLE2142 device is a high-performance, internally compensated operational amplifier built using the Texas Instruments complementary bipolar Excalibur™ process. It is a pin-compatible upgrade to standard industry products.

The design incorporates an input stage that simultaneously achieves low audio-band noise of $10.5 \text{ nV/}\sqrt{\text{Hz}}$ with a 10-Hz 1/f corner and symmetrical 40-V/µs slew rate typically with loads up to 800 pF. The resulting low distortion and high power bandwidth are important in high-fidelity audio applications. A fast settling time of 340 ns to 0.1% of a 10-V step with a 2-k Ω /100-pF load is useful in fast actuator/positioning drivers. Under similar test conditions, settling time to 0.01% is 400 ns.

The device is stable with capacitive loads up to 10 nF, although the 6-MHz bandwidth decreases to 1.8 MHz at this high loading level. As such, the TLE2142 is useful for low-droop sample-and-holds and direct buffering of long cables, including 4-mA to 20-mA current loops.

The special design also exhibits an improved insensitivity to inherent integrated circuit component mismatches as is evidenced by a $500-\mu V$ maximum offset voltage and $1.7-\mu V/^{\circ}C$ typical drift. Minimum common-mode rejection ratio and supply-voltage rejection ratio are 85 dB and 90 dB, respectively.

Device performance is relatively independent of supply voltage over the $\pm 2\text{-V}$ to $\pm 22\text{-V}$ range. Inputs can operate between $V_{CC-} - 0.3$ V to $V_{CC+} - 1.8$ V without inducing phase reversal, although excessive input current may flow out of each input exceeding the lower common-mode input range. The all-npn output stage provides a nearly rail-to-rail output swing of $V_{CC-} + 0.1$ V to $V_{CC+} - 1$ V under light current-loading conditions. The device can sustain shorts to either supply, because output current is internally limited, but care must be taken to ensure that maximum package power dissipation is not exceeded.

The TLE2142 can also be used as a comparator. Differential inputs of $V_{CC\pm}$ can be maintained without damage to the device. Open-loop propagation delay with TTL supply levels is typically 200 ns. This gives a good indication as to output stage saturation recovery when the device is driven beyond the limits of recommended output swing.

The TLE2142 device is available in industry-standard 8-pin small-outline (D) packages. The device is characterized for operation from -40°C to 125°C.

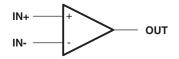


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Excalibur is a trademark of Texas Instruments.



SYMBOL (EACH AMPLIFIER)



ORDERING INFORMATION(1)

T _A	PACK	AGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
-40°C to 125°C	SOIC - D	Reel of 2500	TLE2142QDRQ1	2142Q	

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

⁽²⁾ Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

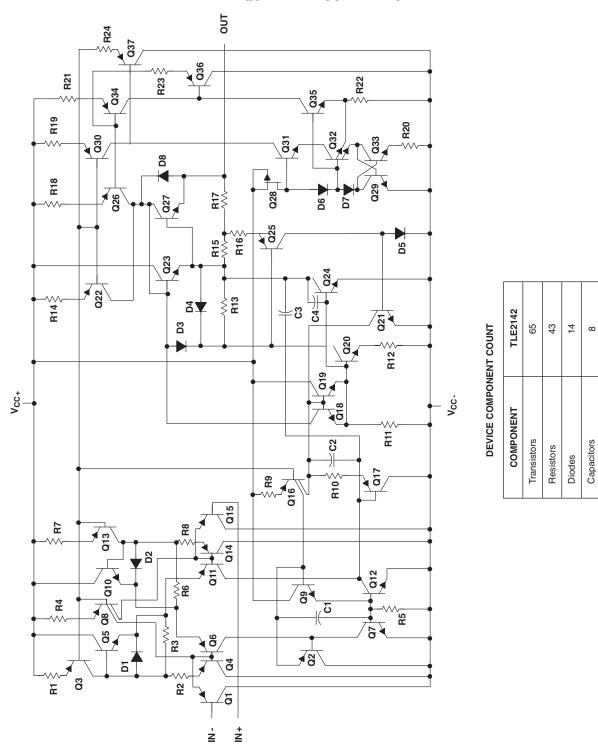


Epi-FET



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EQUIVALENT SCHEMATIC



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ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

V_{CC+}	Supply voltage ⁽²⁾	22 V
V _{CC} -	Supply voltage	–22 V
V_{ID}	Differential input voltage (3)	±44 V
VI	Input voltage range (any input)	V_{CC+} to $(V_{CC-} - 0.3) V$
I _I	Input current (each input)	±1 mA
Io	Output current	±80 mA
	Total current into V _{CC+}	80 mA
	Total current out of V _{CC} _	80 mA
	Duration of short-circuit current at (or below) 25°C (4)	Unlimited
θ_{JA}	Package thermal impedance (5) (6)	97.1°C/W
T _A	Operating free-air temperature range	-40°C to 125°C
T _{stg}	Storage temperature range	−65°C to 150°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C
ESD	Electrostatic discharge rating, Human-body model	500 V

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-} . Differential voltages are at IN+ with respect to IN-. Excessive current flows, if input, are brought below $V_{CC-} = 0.3 \text{ V}$.

The package thermal impedance is calculated in accordance with JESD 51-7.

RECOMMENDED OPERATING CONDITIONS

			MIN	MAX	UNIT
$V_{CC\pm}$	Supply voltage		±2	±22	V
V	Common mode input voltage	V _{CC} = 5 V	0	2.7	V
V_{IC}	Common-mode input voltage	$V_{CC\pm} = \pm 15 \text{ V}$	-15	12.7	V
T _A	Operating free-air temperature		-40	125	°C

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The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

ELECTRICAL CHARACTERISTICS

 $V_{CC} = 5 \text{ V}$, at specified free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	T _A ⁽¹⁾	MIN	TYP	MAX	UNIT	
V	Input offeet veltege	V 25 V D 50 O V 25 V	25°C		220	1900	\/	
V_{IO}	Input offset voltage	$V_{O} = 2.5 \text{ V}, R_{S} = 50 \Omega, V_{IC} = 2.5 \text{ V}$	Full range			2600	μV	
α_{VIO}	Temperature coefficient of input offset voltage	$V_{O} = 2.5 \text{ V}, R_{S} = 50 \Omega, V_{IC} = 2.5 \text{ V}$	Full range		1.7		μV/°C	
1	Input offset current	$V_{O} = 2.5 \text{ V}, R_{S} = 50 \Omega, V_{IC} = 2.5 \text{ V}$	25°C		8	100	nA	
I _{IO}	input onset current	$V_0 = 2.5 \text{ V}, \ \Pi_S = 50 \ \Omega, \ V_{IC} = 2.5 \text{ V}$	Full range			200	IIA	
l	Input bias current	$V_{O} = 2.5 \text{ V}, R_{S} = 50 \Omega, V_{IC} = 2.5 \text{ V}$	25°C		-0.8	-2	μΑ	
I _{IB}	input bias current	V _O = 2.3 V, n _S = 30 Ω, V _{IC} = 2.3 V	Full range			-2.3	μΑ	
V_{ICR}	Common-mode input	$R_S = 50 \Omega$	25°C	0 to 3	–0.3 to 3.2		V	
VICR	voltage range	ng = 30 12	Full range	0 to 2.7	–0.3 to 2.9			
		$I_{OH} = -150 \mu A$		3.9	4.1			
		$I_{OH} = -1.5 \text{ mA}$	25°C	3.8	4		V	
V	High lovel output voltege	I _{OH} = -15 mA		3.4	3.7			
V _{OH}	High-level output voltage	$I_{OH} = -100 \mu A$		3.75			V	
		$I_{OH} = -1 \text{ mA}$	Full range	3.65				
		$I_{OH} = -10 \text{ mA}$		3.45				
		I _{OL} = 150 μA			75	125	mV	
		I _{OL} = 1.5 mA	25°C		150	225		
V	Low-level output voltage	I _{OL} = 15 mA			1.2	1.4	V	
V_{OL}	Low-level output voltage	$I_{OL} = 100 \mu A$				200	mV	
		I _{OL} = 1 mA	Full range			250	IIIV	
		I _{OL} = 10 mA				1.25	V	
۸	Large-signal differential	$V_{IC} = \pm 2.5 \text{ V}, R_{L} = 2 \text{ k}\Omega,$	25°C	50	220		V/mV	
A_{VD}	voltage amplification	$V_0 = 1 \text{ V to } -1.5 \text{ V}$	Full range	5			V/IIIV	
ri	Input resistance		25°C		70		МΩ	
c _i	Input capacitance		25°C		2.5		pF	
z _o	Open-loop output impedance	f = 1 MHz	25°C		30		Ω	
CMDD	Common mode rejection ratio	V V (min) D F0.0	25°C	85	118		٩D	
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}(min), R_S = 50 \Omega$	Full range	80			dB	
k	Supply-voltage rejection ratio	V +2.5.V to +1.5.V B 50.0	25°C	90	106		dB	
k _{SVR}	Supply-voltage rejection ratio $(\Delta V_{CC\pm}/\Delta V_{IO})$	$V_{CC\pm} = \pm 2.5 \text{ V to } \pm 15 \text{ V}, R_S = 50 \Omega$	Full range	85			uВ	
	Cumply augrent	V 25 V No lood V 25 V	25°C		6.6	8.8	m 1	
Icc	Supply current	$V_O = 2.5 \text{ V}$, No load, $V_{IC} = 2.5 \text{ V}$	Full range			9.2	mA	

⁽¹⁾ Full range is -40° C to 125° C.

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OPERATING CHARACTERISTICS

 $V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C} \text{ (unless otherwise noted)}$

	PARAMETER	TEST COND	ITIONS	MIN TYP	MAX	UNIT
SR+	Positive slew rate	$A_{VD} = -1, R_L = 2 k\Omega^{(1)}, C_L$	= 500 pF	45		V/µs
SR-	Negative slew rate	$A_{VD} = -1, R_L = 2 k\Omega^{(1)}, C_L$	= 500 pF	42		V/µs
	Cattling time	A 1 0 5 V atom	To 0.1%	0.16		
t _s	Settling time	$A_{VD} = -1$, 2.5-V step	To 0.01%	0.22		μs
V	Faviralent input paies valtage	D 20 0	f = 10 Hz	15		nV/√ Hz
V _n	Equivalent input noise voltage	$R_S = 20 \Omega$	f = 1 kHz	10.5		11 V / \\\\\\\
V	Peak-to-peak equivalent input	f = 0.1 Hz to 1 Hz	0.48			
$V_{n(PP)}$	noise voltage	f = 0.1 Hz to 10 Hz	0.51		μV	
	Carries la est insertencia a coment	f = 10 Hz	1.92		α Δ / · / I I =	
In	Equivalent input noise current	f = 1 kHz		0.5		pA/√Hz
THD+N	Total harmonic distortion plus noise	$V_O = 1 \text{ V to 3 V}, R_L = 2 \text{ k}\Omega$ f = 10 kHz	$^{(1)}, A_{VD} = 2,$	0.0052		%
B ₁	Unity-gain bandwidth	$R_L = 2 k\Omega^{(1)}, C_L = 100 pF$		5.9		MHz
	Gain-bandwidth product	$R_L = 2 k\Omega^{(1)}, C_L = 100 pF, f = 100 kHz$		5.8		MHz
BOM	Maximum output-swing bandwidth	$V_{O(PP)} = 2 \text{ V}, R_L = 2 \text{ k}\Omega^{(1)},$	A _{VD} = 1, C _L = 100 pF	660		kHz
φ _m	Phase margin at unity gain	$R_L = 2 k\Omega^{(1)}, C_L = 100 pF$		57		٥

⁽¹⁾ R_L terminated at 2.5 V.

ELECTRICAL CHARACTERISTICS

 $V_{CC} = \pm 15 \text{ V}$, at specified free-air temperature (unless otherwise noted)

	PARAMETER	TEST CO	NDITIONS	T _A ⁽¹⁾	MIN	TYP	MAX	UNIT	
M	haran affarah walka wa	V 0. D 50.0		25°C		290	1200		
V_{IO}	Input offset voltage	$V_{IC} = 0$, $R_S = 50 \Omega$		Full range			2000	μV	
α_{VIO}	Temperature coefficient of input offset voltage	$V_{IC} = 0$, $R_S = 50 \Omega$		Full range		1.7		μV/°C	
ı	Innut offeet ourrent	V 0 D 50 O		25°C		7	100	~ ^	
I _{IO}	Input offset current	$V_{IC} = 0$, $R_S = 50 \Omega$		Full range			250	nA	
	Laurent Indonesia and American	V 0. D 50.0		25°C		-0.7	-1.5	^	
I _{IB}	Input bias current	$V_{IC} = 0$, $R_S = 50 \Omega$		Full range			-1.8	μΑ	
M	Common-mode input	D 50.0		25°C	–15 to 13	–15.3 to 13.2		V	
V _{ICR}	voltage range	$R_S = 50 \Omega$		Full range	–15 to 12.7	–15.3 to 12.9			
		$I_{O} = -150 \mu\text{A}$			13.8	14.1			
		$I_{O} = -1.5 \text{ mA}$		25°C	13.7	14			
V	Maximum positive peak	$I_O = -15 \text{ mA}$			13.3	13.7		V	
V_{OM+}	output voltage swing	$I_{O} = -100 \mu A$			13.7			V	
		$I_O = -1 \text{ mA}$		Full range	13.6				
		$I_O = -10 \text{ mA}$			13.3				
		I _O = 150 μA		-14.7	-14.9				
	, Maximum negative peak	I _O = 1.5 mA	25°C	-14.5	-14.8		V		
\/		I _O = 15 mA		-13.4	-13.8				
V_{OM-}	output voltage swing	I _O = 100 μA		-14.6					
		I _O = 1 mA		Full range	-14.5				
		I _O = 10 mA			-13.4				
^	Large-signal differential	V 110 V D 01	.0	25°C	100	450		\//\/	
A_{VD}	voltage amplification	$V_{O} = \pm 10 \text{ V}, R_{L} = 2 \text{ k}$	(12	Full range	20			V/mV	
r _i	Input resistance			25°C		65		МΩ	
Ci	Input capacitance			25°C		2.5		pF	
z _o	Open-loop output impedance	f = 1 MHz		25°C		30		Ω	
CMDD	Commence models well-still motion			50.0	25°C	85	108		40
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}(min), R_S =$	= 50 Ω	Full range	80			dB	
ı.	Supply-voltage rejection ratio	V 10 5 V 45 145	. V D _ 50.0	25°C	90	106		40	
k _{SVR}	$(\Delta V_{CC\pm}/\Delta V_{IO})$	$V_{CC\pm} = \pm 2.5 \ V \ 10 \pm 15$	$V_{CC\pm} = \pm 2.5 \text{ V to } \pm 15 \text{ V}, R_S = 50 \Omega$					dB	
	Chart aircuit autant anna at	V 0	$V_{ID} = 1 V$	0500	-25	-50		- mA	
los	Short-circuit output current V	V _O = 0	$V_{ID} = -1 V$	25°C	20	31			
ı	Cumply aggreent	V ₂ = 0. No load, V ₁₂ = 2.5 V		25°C		6.9	9	m ^	
I _{CC}	Supply current	$V_O = 0$, No load, $V_{IC} = 2.5 \text{ V}$	= ∠.5 V	Full range			9.4	mA	

⁽¹⁾ Full range is -40°C to 125°C.

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OPERATING CHARACTERISTICS

 $V_{CC} = \pm 15 \text{ V}, T_A = 25^{\circ}\text{C} \text{ (unless otherwise noted)}$

	PARAMETER	TEST COND	ITIONS	MIN	TYP	MAX	UNIT
SR+	Positive slew rate	$A_{VD} = -1, R_L = 2 k\Omega, C_L = 1$	00 pF	27	45		V/µs
SR-	Negative slew rate	$A_{VD} = -1, R_L = 2 k\Omega, C_L = 1$	00 pF	27	42		V/µs
	Cattling time	A 1 10 V stop	To 0.1%		0.34		
t _s	Settling time	$A_{VD} = -1$, 10-V step	To 0.01%		0.4		μs
V	Facilitation of the college	D 00.0	f = 10 Hz	·	15		->///
V _n	Equivalent input noise voltage	$R_S = 20 \Omega$	f = 1 kHz	·	10.5		nV/√Hz
, Peak-to-peak equivalent input		f = 0.1 Hz to 1 Hz		0.48		\/	
	noise voltage	f = 0.1 Hz to 10 Hz	·	0.51		μV	
	Carries la est inservir se incoment	f = 10 Hz	·	1.89		n A /s/ Uz	
'n	Equivalent input noise current	f = 1 kHz	·	0.47		— pA/√Hz	
THD+N	Total harmonic distortion plus noise	$V_{O(PP)} = 20 \text{ V}, R_L = 2 \text{ k}\Omega, A$	_{VD} = 10, f = 10 kHz	·	0.01		%
B ₁	Unity-gain bandwidth	$R_L = 2 k\Omega$, $C_L = 100 pF$	× /		6		MHz
	Gain-bandwidth product	$R_L = 2 k\Omega, C_L = 100 pF, f = 100 kHz$		·	5.9		MHz
вом	Maximum output-swing bandwidth	V _{O(PP)} = 20 V, A _{VD} = 1, R _L =		668		kHz	
φ _m	Phase margin at unity gain	$R_L = 2 k\Omega$, $C_L = 100 pF$		·	58		٥

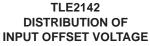
TYPICAL CHARACTERISTICS

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CMRR	Common made rejection ratio		vs Frequency	Figure 17			
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I _{CC}	Supply current		vs Free-air temperature	Figure 22			
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	Gain margin		vs Load capacitance Figure 3				
φ _m	Phase margin		vs Load capacitance Figure 3				

INSTRUMENTS

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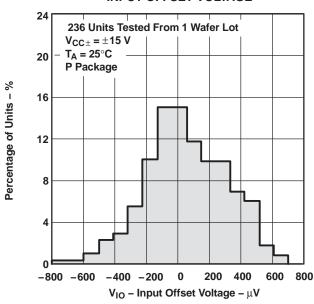
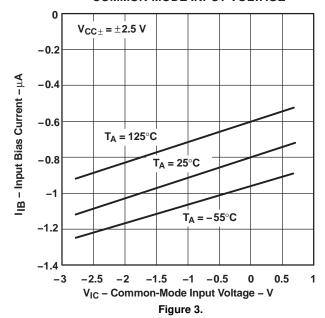
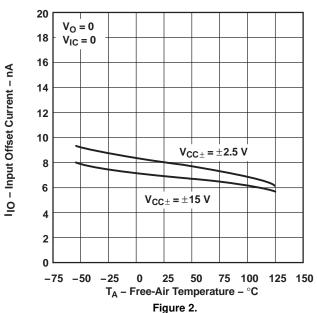


Figure 1.
INPUT BIAS CURRENT

vs COMMON-MODE INPUT VOLTAGE

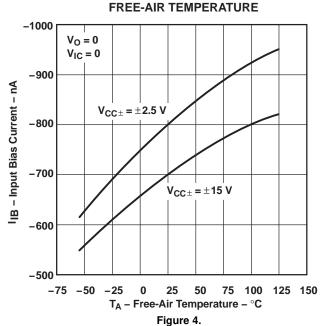


INPUT OFFSET CURRENT vs FREE-AIR TEMPERATURE



INPUT BIAS CURRENT

VS



MAXIMUM PEAK OUTPUT VOLTAGE

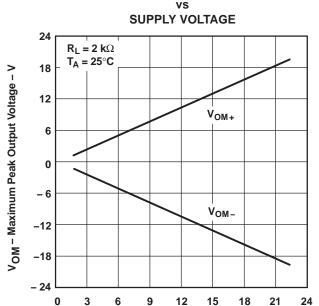
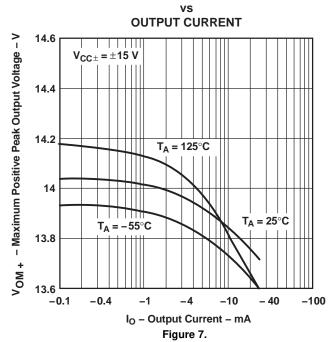


Figure 5. MAXIMUM POSITIVE PEAK OUTPUT VOLTAGE

V_{CC±} - Supply Voltage - V



MAXIMUM PEAK OUTPUT VOLTAGE vs

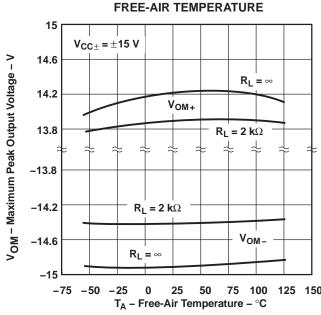
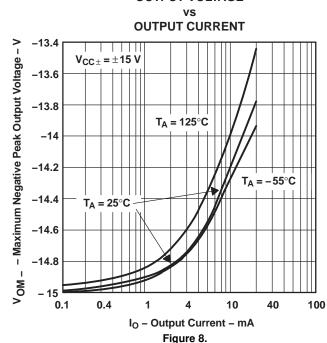
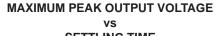


Figure 6.

MAXIMUM NEGATIVE PEAK
OUTPUT VOLTAGE







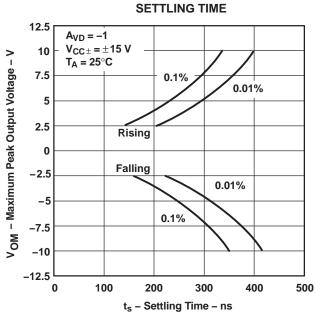
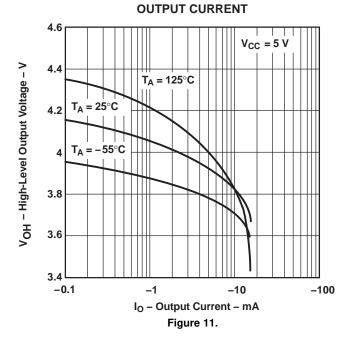


Figure 9.
HIGH-LEVEL OUTPUT VOLTAGE
vs



MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE

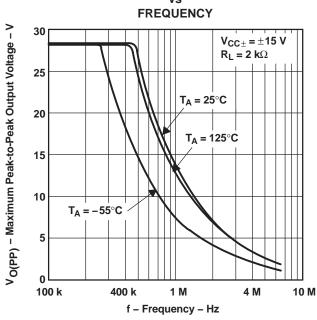
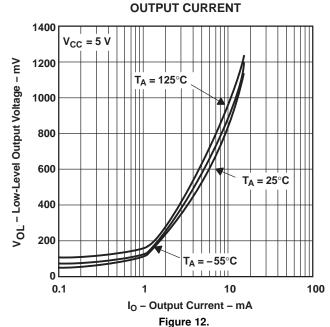


Figure 10.
LOW-LEVEL OUTPUT VOLTAGE
vs



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LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

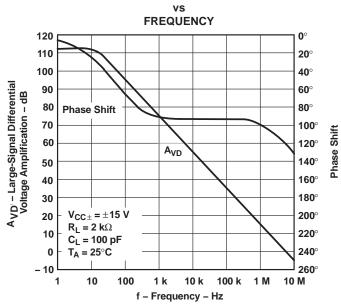
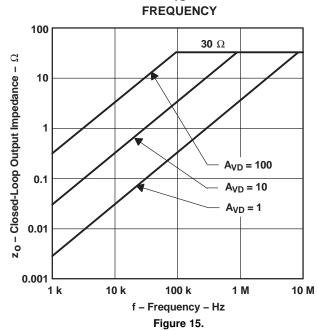
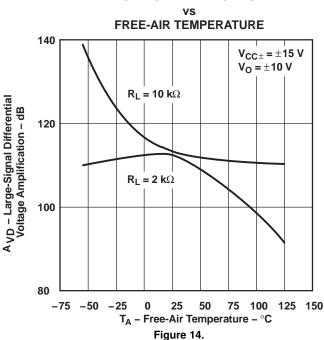


Figure 13.
CLOSED-LOOP OUTPUT IMPEDANCE
vs

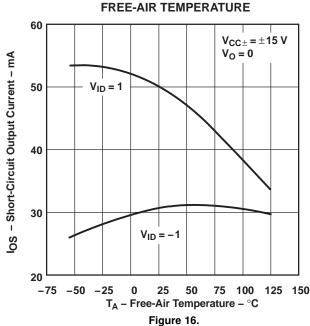


LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION



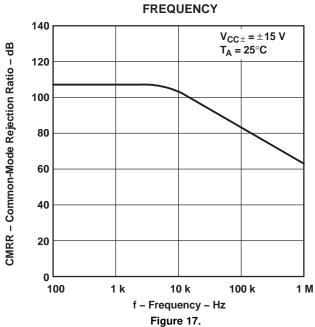
SHORT-CIRCUIT OUTPUT CURRENT



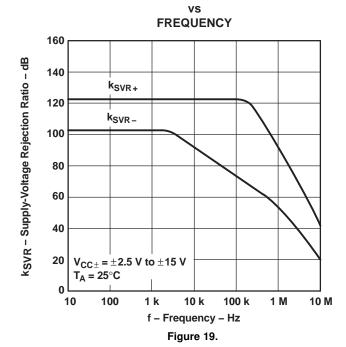




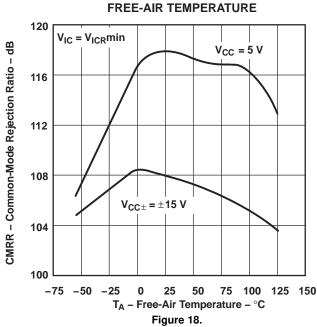




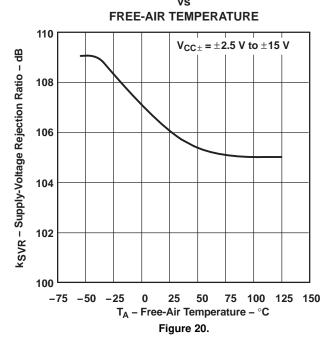
SUPPLY-VOLTAGE REJECTION RATIO

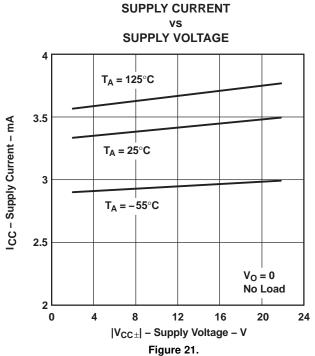


COMMON-MODE REJECTION RATIO vs

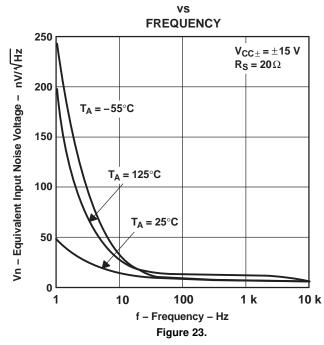


SUPPLY-VOLTAGE REJECTION RATIO





EQUIVALENT INPUT NOISE VOLTAGE



SUPPLY CURRENT vs

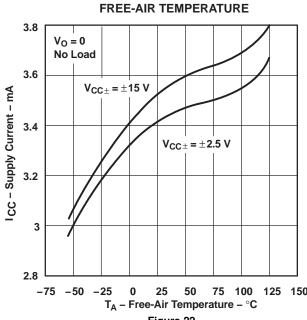
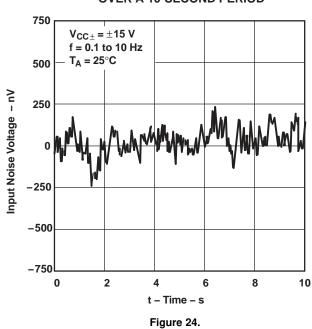
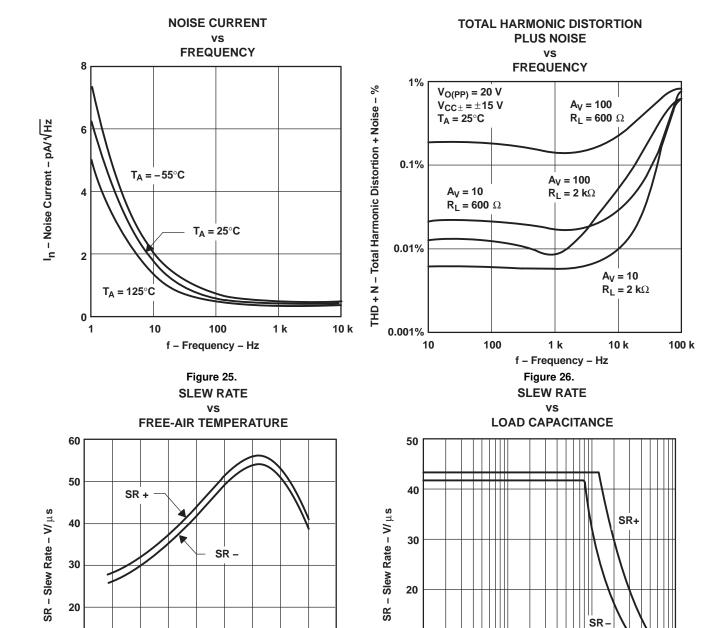


Figure 22. INPUT NOISE VOLTAGE OVER A 10-SECOND PERIOD



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25

50

T_A – Free-Air Temperature – °C Figure 27.

75 100 125 150

 $V_{CC\pm} = \pm 15 \text{ V}$

 $A_{VD} = -1$

 $R_L = 2 k\Omega$

-75 -50 -25

 $C_L = 500 pF$

10

10

 $V_{CC\pm} = \pm 15 \text{ V}$

0.1

C_L - Load Capacitance - nF

Figure 28.

 $A_{VD} = -1$

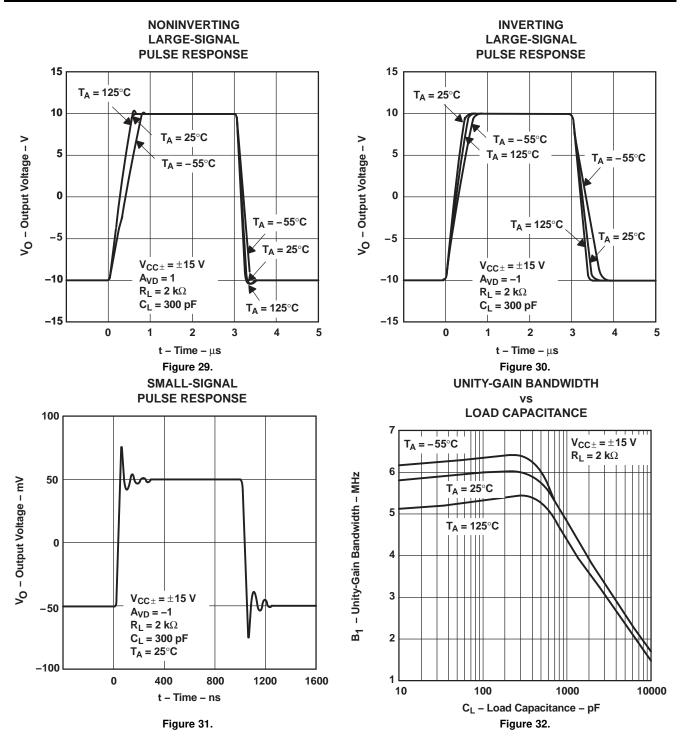
T_A = 25°C

10

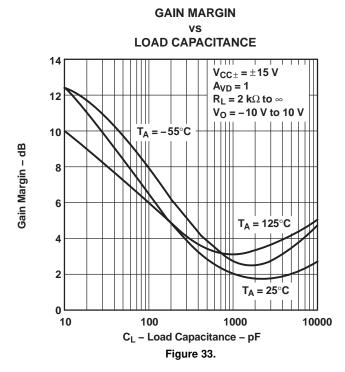
0.01

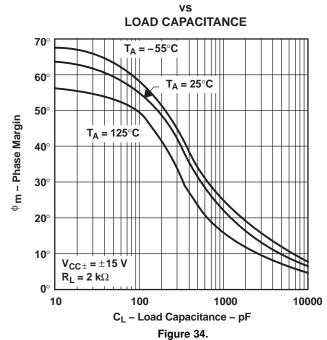












PHASE MARGIN



10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TLE2142QDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2142Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TLE2142-Q1:



PACKAGE OPTION ADDENDUM

10-Dec-2020

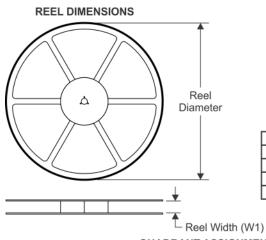
Military: TLE2142M

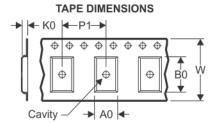
NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

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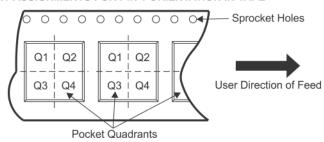
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

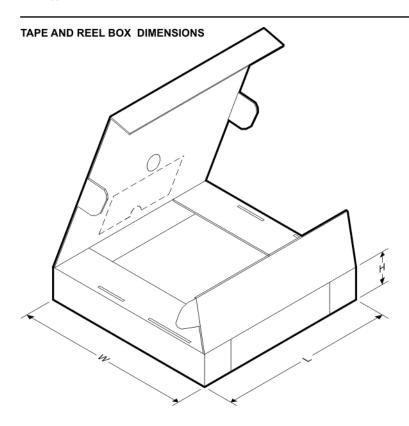
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLE2142QDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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*All dimensions are nominal

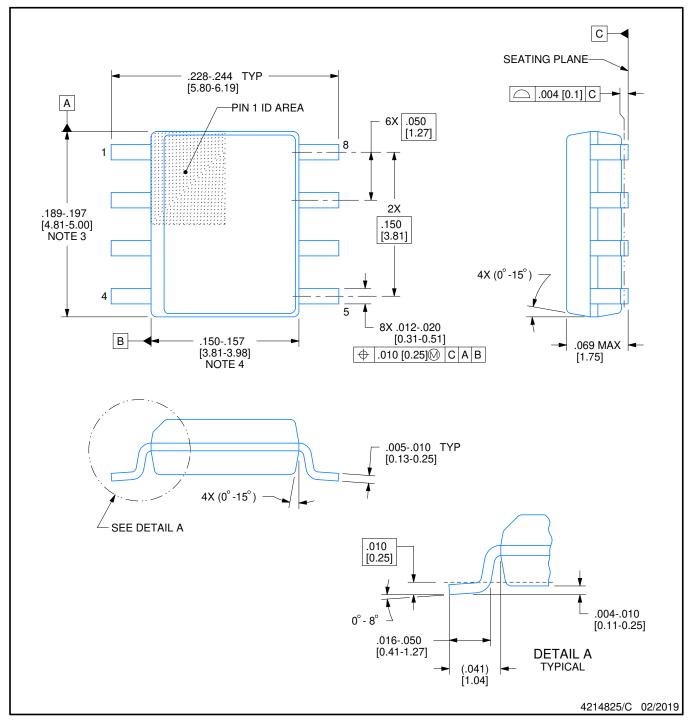
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TLE2142QDRQ1	SOIC	D	8	2500	340.5	336.1	25.0	

PACKAGE OUTLINE



SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

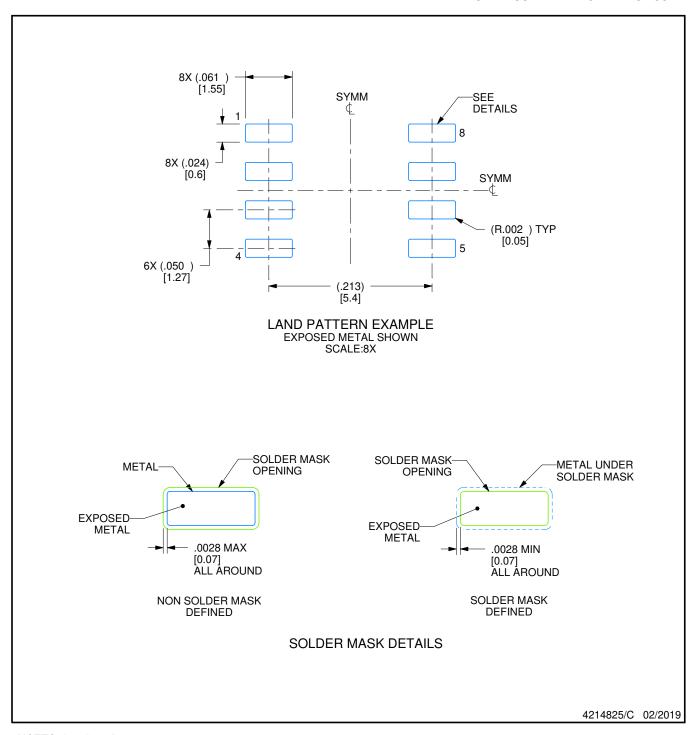


NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



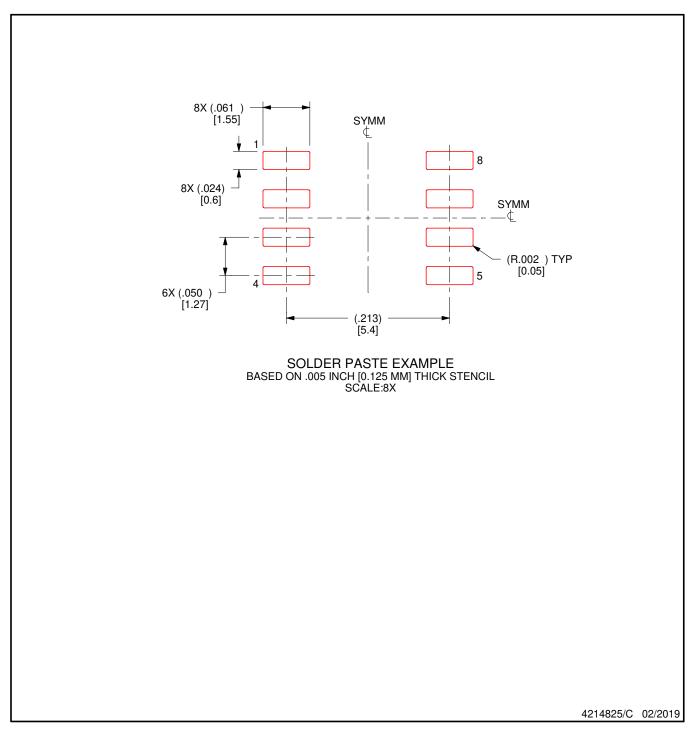
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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